

10598123_QUESTIONS

Titles of most frequently occurring classifications of patents returned from a search of 10598123 on Mar 09, 2010

- 6 136/249 (4 OR, 2 XR)
 - Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
 - 136/243 . PHOTOELECTRIC
 - 136/244 . Panel or array
 - 136/249 . . . Monolithic semiconductor
- 4 365/201 (3 OR, 1 XR)
 - Class 365 STATIC INFORMATION STORAGE AND RETRIEVAL
 - 365/189.011 . READ/WRITE CIRCUIT
 - 365/201 . . Testing
- 3 438/396 (3 OR, 0 XR)
 - Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 - 438/381 . MAKING PASSIVE DEVICE (E.G., RESISTOR, CAPACITOR, ETC.)
 - 438/396 . . Stacked capacitor
- 3 429/185 (0 OR, 3 XR)
 - Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
 - 429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 - 429/163 . . Cell enclosure structure, e.g., housing, casing, container, cover, etc.
 - 429/185 . . . Having seal feature
- 3 438/933 (0 OR, 3 XR)
 - Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 - 438/933 . GERMANIUM OR SILICON OR GE-SILICON III-V
- 3 438/74 (1 OR, 2 XR)
 - Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 - 438/48 . MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRIC SIGNAL
 - 438/57 . . Responsive to electromagnetic radiation
 - 438/73 . . . Making electromagnetic responsive array
 - 438/74 . . . Vertically arranged (e.g., tandem stacked, etc.)
- 2 257/461 (0 OR, 2 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/414 . RESPONSIVE TO NONELECTRIC SIGNAL (E.G., CHEMICAL, STRESS, LIGHT, OR MAGNETIC FIELD SENSORS)
 - 257/428 . . Electromagnetic or particle radiation
 - 257/431 . . . Light
 - 257/461 . . . Light responsive pn junction
- 2 712/15 (2 OR, 0 XR)
 - Class 712 ELECTRICAL COMPUTERS AND DIGITAL PROCESSING SYSTEMS: PROCESSING ARCHITECTURES AND INSTRUCTION PROCESSING (E.G., PROCESSORS)
 - 712/1 . PROCESSING ARCHITECTURE
 - 712/10 . . Array processor
 - 712/11 . . . Array processor element interconnection
 - 712/15 . . . Reconfiguring
- 2 438/970 (0 OR, 2 XR)
 - Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 - 438/970 . SPECIFIED ETCH STOP MATERIAL
- 2 257/E27.089 (0 OR, 2 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE

DI CODES)

257/E27.001 ...DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E. G., INTEGRATED CIRCUIT DEVICE (EPO)

257/E27.009 ...Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or including integrated passive circuit elements (EPO)

257/E27.01 ...With semiconductor substrate only (EPO)

257/E27.07 ...Including a plurality of individual components in a repetitive configuration (EPO)

257/E27.081 ...Including field-effect component (EPO)

257/E27.084 ...Dynamic random access memory, DRAM structure (EPO)

257/E27.085 ...One-transistor memory cell structure, i.e., each memory cell containing only one transistor (EPO)

257/E27.086 ...Storage electrode stacked over the transistor

257/E27.089 ...Storage electrode having multiple wings (EPO)

2 365/63 (0 OR, 2 XR)

Class 365 STATIC INFORMATION STORAGE AND RETRIEVAL

365/63 ...INTERCONNECTION ARRANGEMENTS

2 438/586 (0 OR, 2 XR)

Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS

438/584 ...COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL

438/585 ...Insulated gate formation

438/586 ...Combined with formation of ohmic contact to semiconductor region

2 257/E27.101 (0 OR, 2 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E. G., TRANSISTORS, SOLID-STATE

DI CODES)

257/E27.001 ...DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E. G., INTEGRATED CIRCUIT DEVICE (EPO)

257/E27.009 ...Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or including integrated passive circuit elements (EPO)

257/E27.01 ...With semiconductor substrate only (EPO)

257/E27.07 ...Including a plurality of individual components in a repetitive configuration (EPO)

257/E27.081 ...Including field-effect component (EPO)

257/E27.098 ...Static random access memory, SRAM structure (EPO)

257/E27.101 ...Load element being a resistor (EPO)

2 429/59 (1 OR, 1 XR)

Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS

429/57 ...SEALED CELL HAVING GAS PREVENTION OR ELIMINATION MEANS

429/59 ...Prevention or elimination means is one of the cell electrodes or is electrically connected to an electrode

2 429/157 (1 OR, 1 XR)

Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS

429/122 ...CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS

429/149 ...Plural cells

429/156 ...Complete cells

429/157 ...In end-to-end contact, e.g., stacked button-type cell, etc.

2 429/162 (0 OR, 2 XR)

Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,

AND PROCESS

429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/162 ... Flat-type unit cell and specific unit cell components

2 429/210 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ... Electrode
429/210 ... Bipolar type

2 429/90 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/90 . WITH MEASURING, TESTING, OR INDICATING MEANS

2 429/217 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ... Electrode
429/212 ... Having active material with organic component
429/217 ... Organic component is a binder

2 429/223 (1 OR, 1 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ... Electrode
429/218.1 ... Chemically specified inorganic electrochemically active
material containing
429/223 ... Nickel component is active material

2 257/E27.129 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE
DIODES)
257/E27.001 . DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER
SOLID-STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT
DEVICE (EPO)
257/E27.122 ... Including active semiconductor component sensitive to
infrared radiation, light, or electromagnetic radiation of a shorter wavelength
(EPO)
257/E27.127 ... Device controlled by radiation (EPO)
257/E27.128 ... With at least one potential barrier or surface barrier
(EPO)
257/E27.129 ... In a repetitive configuration (EPO)

2 257/E31.115 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE
DIODES)
257/E31.001 . SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO
ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF
RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH
RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH
DEVICES, OR OF PARTS THEREOF) (EPO)
257/E31.11 . Detail of nonsemiconductor component of
radiation-sensitive semiconductor device (EPO)
257/E31.113 ... Circuit arrangement of general character for device (EPO)
257/E31.114 ... For device having potential or surface barrier (EPO)

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257/E31.115 Position-sensitive and lateral-effect photodetector
(e.g., quadrant photodiode) (EPO)

2 257/E27.128 (0 OR, 2 XR)
Q ass 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE
DIODES)
257/E27.001 . DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER
SOLID-STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT
DEVICE (EPO)
257/E27.122 ..Including active semiconductor component sensitive to
infrared radiation, light, or electromagnetic radiation of a shorter wavelength
(EPO)
257/E27.127 ...Device controlled by radiation (EPO)
257/E27.128With at least one potential barrier or surface barrier
(EPO)

2 429/218.1 (0 OR, 2 XR)
Q ass 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ..Electrode
429/218.1 ...Chemically specified inorganic electrochemically active
material containing

2 716/8 (1 OR, 1 XR)
Q ass 716 DATA PROCESSING: DESIGN AND ANALYSIS OF CIRCUIT OR
SEMICONDUCTOR MASK
716/1 . CIRCUIT DESIGN
716/8 ..Floorplanning

2 204/252 (0 OR, 2 XR)
Q ass 204 CHEMISTRY: ELECTRICAL AND WAVE ENERGY
204/193 . APPARATUS
204/194 ..Electrolytic
204/242 ...Cells
204/252Diaphragm type

2 429/337 (0 OR, 2 XR)
Q ass 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS
429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/188 ..Include electrolyte chemically specified and method
429/324 ...Chemically specified organic solvent containing
429/336 ...Heteroring in the organic solvent
429/337Oxygen is the only ring heteroatom in the heteroring
(e.g., di-oxolane, gamma butyrolactone, etc.)

2 438/73 (1 OR, 1 XR)
Q ass 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/48 . MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL
438/57 ..Responsive to electromagnetic radiation
438/73 ...Making electromagnetic responsive array

2 257/E25.007 (0 OR, 2 XR)
Q ass 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE
DIODES)
257/E25.001 . ASSEMBLIES CONSISTING OF PLURALITY OF INDIVIDUAL
SEMICONDUCTOR OR OTHER SOLID-STATE DEVICES (EPO)
257/E25.002 ..All devices being of same type, e.g., assemblies of
rectifier diodes (EPO)
257/E25.003 ...Devices not having separate containers (EPO)

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257/E25.004 Devices responsive or sensitive to electromagnetic radiation, e.g., infrared radiation, adapted for conversion of radiation into electrical energy or for control of electrical energy by such radiation (EPO)
 257/E25.006 Stacked arrangements of devices (EPO)
 257/E25.007 Devices being solar cells (EPO)

2 136/262 (0 OR, 2 XR)

Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
 136/243 . PHOTOELECTRIC
 136/252 . Cells
 136/262 . . . Gallium containing

2 257/E31.014 (0 OR, 2 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/E31.001 . SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)

257/E31.002 . . Characterized by semiconductor body (EPO)
 257/E31.003 . . . Characterized by semiconductor body material (EPO)
 257/E31.004 Inorganic materials (EPO)
 257/E31.011 Including, apart from doping material or other impurity, only Group IV element (EPO)
 257/E31.014 Characterized by doping material (EPO)

2 257/E31.021 (0 OR, 2 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/E31.001 . SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)

257/E31.002 . . Characterized by semiconductor body (EPO)
 257/E31.003 . . . Characterized by semiconductor body material (EPO)
 257/E31.004 Inorganic materials (EPO)
 257/E31.019 Including, apart from doping material or other impurity, only Group III-V compound (EPO)
 257/E31.02 For device having potential or surface barrier (EPO)
 257/E31.021 Characterized by doping material GaAlAs, InGaAs, InGaAsP (EPO)

2 438/94 (0 OR, 2 XR)

Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/48 . MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRIC SIGNAL
 438/57 . . Responsive to electromagnetic radiation
 438/93 . . . Compound semiconductor
 438/94 Heterojunction